

Remarks

This is in response to the Office Action dated December 5, 2001. Claims 9-14 have been canceled without prejudice. Claims 19-23 have been added. Claims 1-8 and 15-23 are currently pending. Reexamination and reconsideration are respectfully requested.

Claims 9-14 have been canceled without prejudice to prosecute these claims at a later time.

Claims 1-8 and 15-18 were rejected under 35 U.S.C. 102(e) as unpatentable over U.S. Patent No. 5,928,959 to Huckels et al. ("Huckels"). The rejection is respectfully traversed. Applicant respectfully submits that the Examiner has cited no portion of Huckels that describes a "semiconductor device having a DRAM including a cell capacitor formed in a DRAM region of a semiconductor substrate, and a capacitor element formed in an analog element region of the semiconductor substrate" as recited in claim 1. The portions of Huckels as cited by the Examiner including Fig. 1 element 161 and col. 2, lines 34-40, appear to relate to a single trench capacitor DRAM cell. The Examiner has cited no portion of Huckels describing "simultaneously forming" certain structures in a "DRAM including a cell capacitor formed in a DRAM region" and "a capacitor element forming in an analog element region" as recited in claim 1. Accordingly, the rejection should be withdrawn. Claims 2-8 depend from claim 1 and the rejection of these claims should be withdrawn for at least the same reasons as for claim 1.

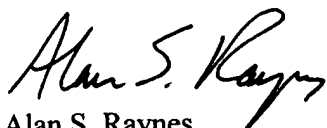
The Examiner's rejection of claim 15 and its dependent claims 16-18 is deficient for at least similar reasons as claim 1 as explained above and should be withdrawn for at least the same reasons as for claim 1. Applicant notes that claim 16 has been amended for clarity.

Applicant has added new dependent claims 19-23. It is believed that no new matter has been entered. Support for claims 19-23 may be found throughout the specification, for example, at pages 21-23, Figs. 10-15 and in the original claims. Examination of the new claims is respectfully requested.

Attached hereto is a marked-up version of the claim changes made by the present amendment. The attached page is captioned "Version with markings to show changes made."

Applicant respectfully submits that claims 1-8 and 15-23 are in condition for allowance. Reexamination and reconsideration are respectfully requested. If, for any reason, the application is not in condition for allowance, the Examiner requested to telephone the undersigned to discuss the steps necessary to place the application into condition for allowance.

Respectfully submitted,

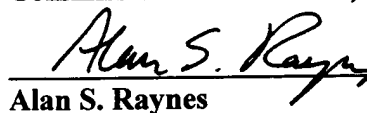


Alan S. Raynes
Reg. No. 39,809
Konrad Raynes Victor & Mann, LLP
315 South Beverly Drive, Suite 210
Beverly Hills, CA 90212
Customer No. 24033
general tele (310) 556-7983
direct tele (310) 871-8448
facsimile (310) 556-7984

Dated: June 4, 2002

Certificate of Mailing

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231 on June 4, 2002.


Alan S. Raynes

June 4, 2002
(Date)

Version With Markings to Show Changes Made

Claim 16 has been amended as follows:

16. (amended) A method according to claim 15, further comprising, prior to forming the storage node of the cell capacitor and the lower electrode of the capacitor element, [form] forming an additional conducting layer and etching the additional conducting layer to form a word line that is a component of the DRAM and to form a connection layer that is located in a common layer of the word line and that is configured to electrically connect the lower electrode to another element in the semiconductor device.